

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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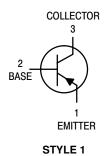
Preferred Device

General Purpose Transistors

PNP Silicon

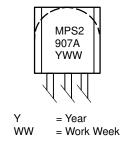


http://onsemi.com





MARKING DIAGRAMS



ORDERING INFORMATION

Device	Package	Shipping
MPS2907A	TO-92	5000 Units/Box
MPS2907ARLRA	TO-92	2000/Tape & Reel
MPS2907ARLRE	TO-92	2000/Ammo Pack
MPS2907ARLRM	TO-92	2000/Ammo Pack
MPS2907ARLRP	TO-92	2000/Ammo Pack

Preferred devices are recommended choices for future use and best overall value.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	VCEO	-60	Vdc
Collector-Base Voltage	V _{CBO}	-60	Vdc
Emitter-Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current – Continuous	IC	-600	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	625 5.0	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.5 12	Watts mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

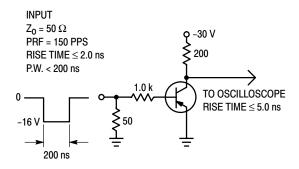
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction to Case	R _θ JC	83.3	°C/W

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS		1			<u>I</u>
Collector–Emitter Breakdown Voltage (Note 1.) (I _C = -10 mAdc, I _B = 0)		V _(BR) CEO	-60	_	Vdc
Collector–Base Breakdown Voltage (I _C = –10 μAdc, I _E = 0)		V _(BR) CBO	-60	_	Vdc
Emitter–Base Breakdown Voltage $(I_E = -10 \mu Adc, I_C = 0)$		V _{(BR)EBO}	-5.0	_	Vdc
Collector Cutoff Current (VCE = -30 Vdc, VEB(off) = -0.5 Vdc)		ICEX	-	-50	nAdc
Collector Cutoff Current (VCB = -50 Vdc, IE = 0) (VCB = -50 Vdc, IE = 0, TA = 150°C)		ICBO	- -	-0.01 -10	μAdc
Base Current (V _{CE} = -30 Vdc, V _{EB(off)} = -0.5 Vdc)		lΒ	-	-50	nAdc
ON CHARACTERISTICS					
$ \begin{array}{c} DC \ Current \ Gain \\ (I_C = -0.1 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -1.0 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -10 \ mAdc, \ V_{CE} = -10 \ Vdc) \\ (I_C = -150 \ mAdc, \ V_{CE} = -10 \ Vdc) \ (No \ (I_C = -500 \ mAdc, \ V_{CE} = -10 $		hFE	75 100 100 100 50	- - - 300 -	-
Collector–Emitter Saturation Voltage (Note 1.) (IC = -150 mAdc, IB = -15 mAdc) (IC = -500 mAdc, IB = -50 mAdc)		V _{CE(sat)}		-0.4 -1.6	Vdc
Base–Emitter Saturation Voltage (Note 1.) (IC = -150 mAdc, IB = -15 mAdc) (IC = -500 mAdc, IB = -50 mAdc)		V _{BE(sat)}	<u>-</u>	-1.3 -2.6	Vdc
SMALL-SIGNAL CHARACTERISTIC	CS				
Current–Gain – Bandwidth Product (Notes 1. and 2.), (I _C = –50 mAdc, V _{CE} = –20 Vdc, f = 100 MHz)		fT	200	-	MHz
Output Capacitance ($V_{CB} = -10 \text{ Vdc}$, $I_E = 0$, $f = 1.0 \text{ MHz}$)		C _{obo}	-	8.0	pF
Input Capacitance (VEB = -2.0 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	-	30	pF
SWITCHING CHARACTERISTICS				•	
Turn-On Time	$(V_{CC} = -30 \text{ Vdc}, I_{C} = -150 \text{ mAdc},$	t _{on}	-	45	ns
Delay Time	$I_{B1} = -15 \text{ mAdc}$) (Figures 1 and 5)	^t d	_	10	ns
Rise Time		t _r	_	40	ns
Turn-Off Time	$(V_{CC} = -6.0 \text{ Vdc}, I_{C} = -150 \text{ mAdc},$	toff	-	100	ns
Storage Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$ (Figure 2)	t _S	-	80	ns
Fall Time		t _f	-	30	ns

^{1.} Pulse Test: Pulse Width $\leq 300~\mu s$, Duty Cycle $\leq 2\%$. 2. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.



INPUT $Z_0 = 50~\Omega$ PRF = 150~PPS $RISE~TIME \le 2.0~ns$ P.W. < 200~ns 1.0~k 37 TO~OSCILLOSCOPE $RISE~TIME \le 5.0~ns$ 200~ns

Figure 1. Delay and Rise Time Test Circuit

Figure 2. Storage and Fall Time Test Circuit

TYPICAL CHARACTERISTICS

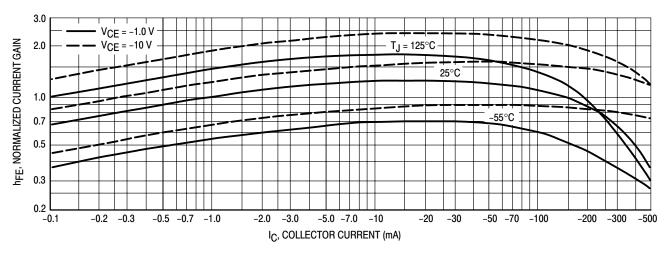


Figure 3. DC Current Gain

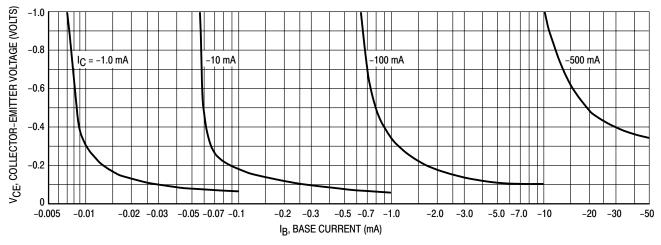
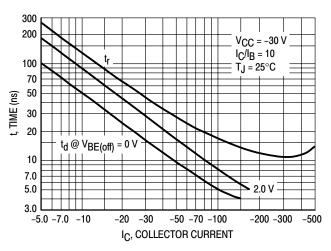


Figure 4. Collector Saturation Region

TYPICAL CHARACTERISTICS

500



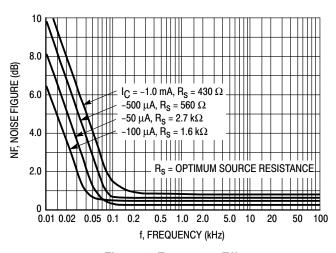
300 $V_{CC} = -30 \text{ V}$ $I_C/I_B = 10$ 200 I_{B1} = I_{B2} T_J = 25°C 100 70 50 $t'_{S} = t_{S} - 1/8 t_{f}$ 30 20 10 7.0 -5.0 -7.0 -10 -30 -50 -70 -100 -200 -300 -500 IC, COLLECTOR CURRENT (mA)

Figure 5. Turn-On Time

Figure 6. Turn-Off Time

TYPICAL SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VCE = 10 Vdc, TA = 25°C

10



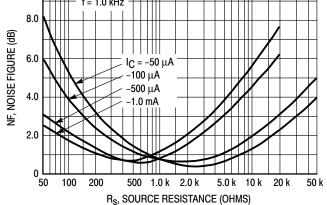
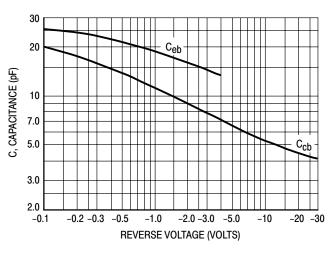


Figure 7. Frequency Effects

Figure 8. Source Resistance Effects

TYPICAL SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE

 $V_{CE} = 10 \text{ Vdc}, T_A = 25^{\circ}C$



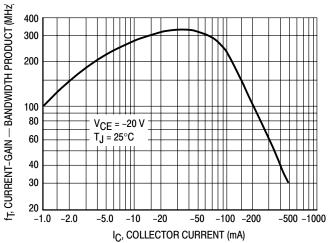


Figure 9. Capacitances

Figure 10. Current-Gain — Bandwidth Product

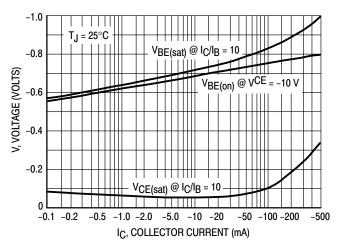


Figure 11. "On" Voltage

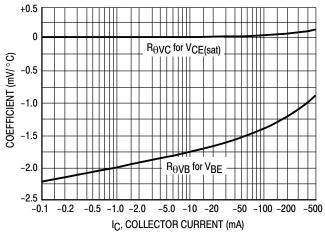
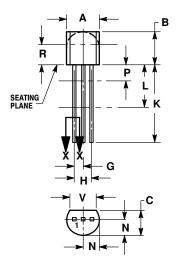


Figure 12. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 TO-226AA CASE 29-11

ISSUE AL





- NOTES:
 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
 4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

Notes

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